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VS-ST230SPbF

RoHS

COMPLIANT

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Phase Control Thyristors (Stud Version), 230 A



PRIMARY CHARACTERISTICS					
I _{T(AV)}	230 A				
V _{DRM} /V _{RRM}	1400 V, 1600 V				
V _{TM}	1.55 V				
I _{GT}	150 mA				
TJ	-40 °C to +125 °C				
Package	TO-93 (TO-209AB)				
Circuit configuration	Single SCR				

FEATURES

- · Center amplifying gate
- International standard case TO-93 (TO-209AB)
- · Hermetic metal case with ceramic insulator
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		230	А			
I _{T(AV)}	T _C	85	°C			
I _{T(RMS)}		360	A			
1	50 Hz	5700	•			
ITSM	60 Hz	5970	- A			
l ² t	50 Hz	163	kA ² s			
1-1	60 Hz	149	KA-S			
V _{DRM} /V _{RRM}		1400 to 1600	V			
t _q	Typical	100	μs			
TJ		-40 to +125	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RA	ATINGS			
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$ I_{DRM} / I_{RRM} MAXIMUM AT $
VS-ST230S	14	1400	1500	30
V3-312303	16	1600	1700	30

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ABSOLUTE MAXIMUM RATINGS	5						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS	
Maximum average on-state current	L	190° condu	ction, half sine	NOV0	230	Α	
at case temperature	I _{T(AV)}		ction, nan sine	wave	85	°C	
Maximum RMS on-state current	I _{T(RMS)}	DC at 78 °C	case temperat	ure	360		
		t = 10 ms	No voltage		5700		
Maximum peak, one-cycle	I	t = 8.3 ms	reapplied		5970	А	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		4800		
		t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	5000		
	l ² t	t = 10 ms	No voltage		163	kA ² s	
Maximum I ² t for fusing		t = 8.3 ms	reapplied		148		
Maximum i-t for fusing		t = 10 ms	100 % V _{RRM}		115	KA-S	
		t = 8.3 ms	reapplied		105		
Maximum I ² √t for fusing	l²√t	t = 0.1 to 10) ms, no voltage	e reapplied	1630	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x \ I_{T(AV)} < I < \pi \ x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.92	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			v	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T _J = T _J maximum			0.88	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			0.81	11152	
Maximum on-state voltage	V_{TM}	I _{pk} = 720 A,	$T_J = T_J maximu$	ım, t _p = 10 ms sine pulse	1.55	V	
Maximum holding current	Ι _Η	T _ 25 °C	anada ayanlıy 1	2 V resistive load	600	mA	
Maximum (typical) latching current	١L	$1_{\rm J} = 25$ C,	anoue supply 1		1000 (300)	IIIA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,$ $t_r \leq$ 1 μs T_J = T_J maximum, anode voltage \leq 80 % V_{DRM}	1000	A/µs
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.0	
Typical turn-off time	tq	I_{TM} = 300 A, T_J = T_J maximum, dI_F/dt = 20 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J maximum linear to 80 \% rated V_{DRM}$	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	30	mA



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TRIGGERING						
DADAMETED	SYMBOL	т				
PARAMETER	STIVIDUL	"	EST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	10	0.0	W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2.	.0	vv
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	3.	.0	А
Maximum peak positive gate voltage	+ V _{GM}		+ < 5 mg	2	0	V
Maximum peak negative gate voltage	- V _{GM}	$T_J = T_J$ maximum,	5.0		v	
				180	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger/	90	150	mA
		T _J = 125 °C	current/voltage are the lowest	40	-	
		T _J = - 40 °C	value which will trigger all units 12	2.9	-	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	V anode to cathode applied	1.8	3.0	V
		T _J = 125 °C	°C		-	
DC gate current not to trigger	I _{GD}		Maximum gate current/voltage not	ot 10		mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.05		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		-40 to 125	°C	
Maximum storage temperature range	T _{Stg}		-40 to 150		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.10	K/W	
Maximum thermal resistance, case to heatsink	R _{thC-hs}	_{IC-hs} Mounting surface, smooth, flat and greased 0.04		r\/ vv	
Mounting torque, \pm 10 %		Non-lubricated threads		N·m	
Mounting torque, ± 10 %		Lubricated threads24.5 (210)		(lbf · in)	
Approximate weight			280	g	
Case style		See dimensions - link at the end of datasheet	TO-93 (TO-2	209AB)	

	ON			
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.016	0.012		
120°	0.019	0.020		
90°	0.025	0.027	$T_J = T_J$ maximum	K/W
60°	0.036	0.037		
30°	0.060	0.060		

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



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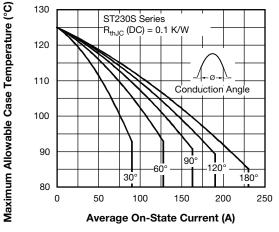


Fig. 1 - Current Ratings Characteristics

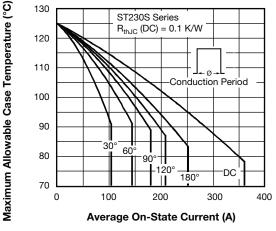


Fig. 2 - Current Ratings Characteristics

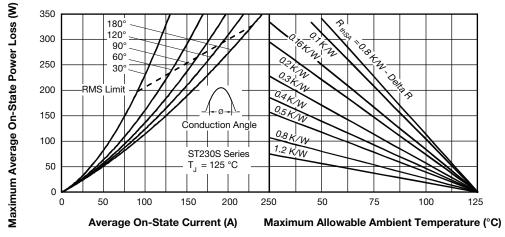
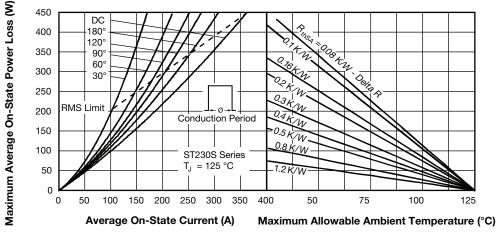


Fig. 3 - On-State Power Loss Characteristics







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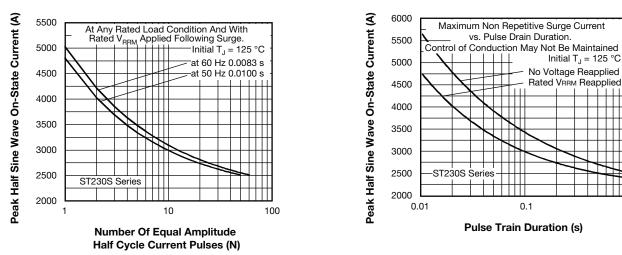


Fig. 5 - Maximum Non-Repetitive Surge Current



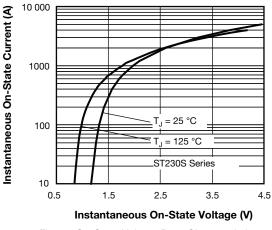
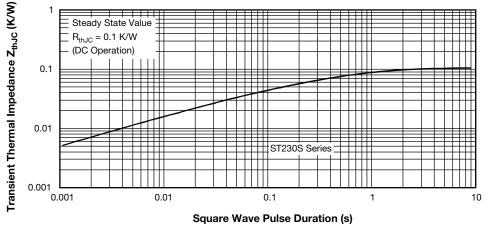
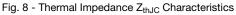


Fig. 7 - On-State Voltage Drop Characteristics





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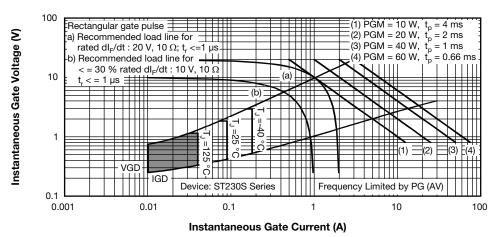


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	ST	23	0	S	16	Р	0	PbF
	1	2	3	4	5	6	7	8	9
	1 - 2 -		nay Sen ristor	niconduc	ctors pro	oduct			
	3 -	Ess	ential pa	art num	ber				
	4 -	0 =	convert	er grade)				
	5 -	S =	compre	ssion bo	onding s	stud			
	6 -	Volt	age coo	de x 100	= V _{RRM}	_I (see V	oltage F	Ratings	table)
	7 -	P =	stud ba	se 3/4"-	16UNF2	2A threa	ads		
	8 -	0 =	eyelet t	erminals	s (gate a	ind auxi	liary ca	thode le	eads)
		1 =	fast-on	terminal	s (gate	and aux	kiliary ca	athode I	eads)
	9 -	Nor	ne = stai	ndard pr	oductio	n			
	-	Pbl	= = lead	(Pb)-fre	e				

Note: For metric device M16 x 1.5 contact factory

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95082			

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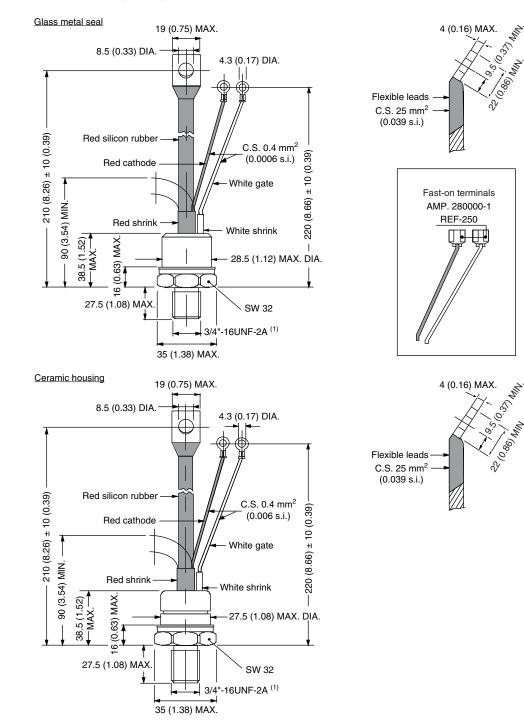
NI.

NIN,



DIMENSIONS in millimeters (inches)

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Note

⁽¹⁾ For metric device: M16 x 1.5 - length 21 (0.83) maximum

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1



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1